



安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

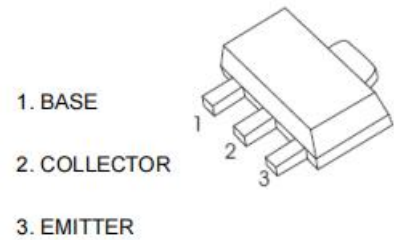
C4375

SOT-89 Bipolar Transistor 双极型三极管

■ Features 特点

NPN Low Voltage 低压

■ Absolute Maximum Ratings 最大额定值



Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Collector-Base Voltage 集电极基极电压	V_{CBO}	30	V
Collector-Emitter Voltage 集电极发射极电压	V_{CEO}	30	V
Emitter-Base Voltage 发射极基极电压	V_{EBO}	5	V
Collector Current 集电极电流	I_C	1500	mA
Power dissipation 耗散功率	$P_C(T_a=25^{\circ}C)$	500	mW
Thermal Resistance Junction-Ambient 热阻	$R_{\theta JA}$	250	$^{\circ}C/W$
Junction and Storage Temperature 结温和储藏温度	T_J, T_{stg}	-55to+150 $^{\circ}C$	

■ Device Marking 产品打标

H_{FE}	100-200(O)	160-320(Y)
Mark	GO	GY

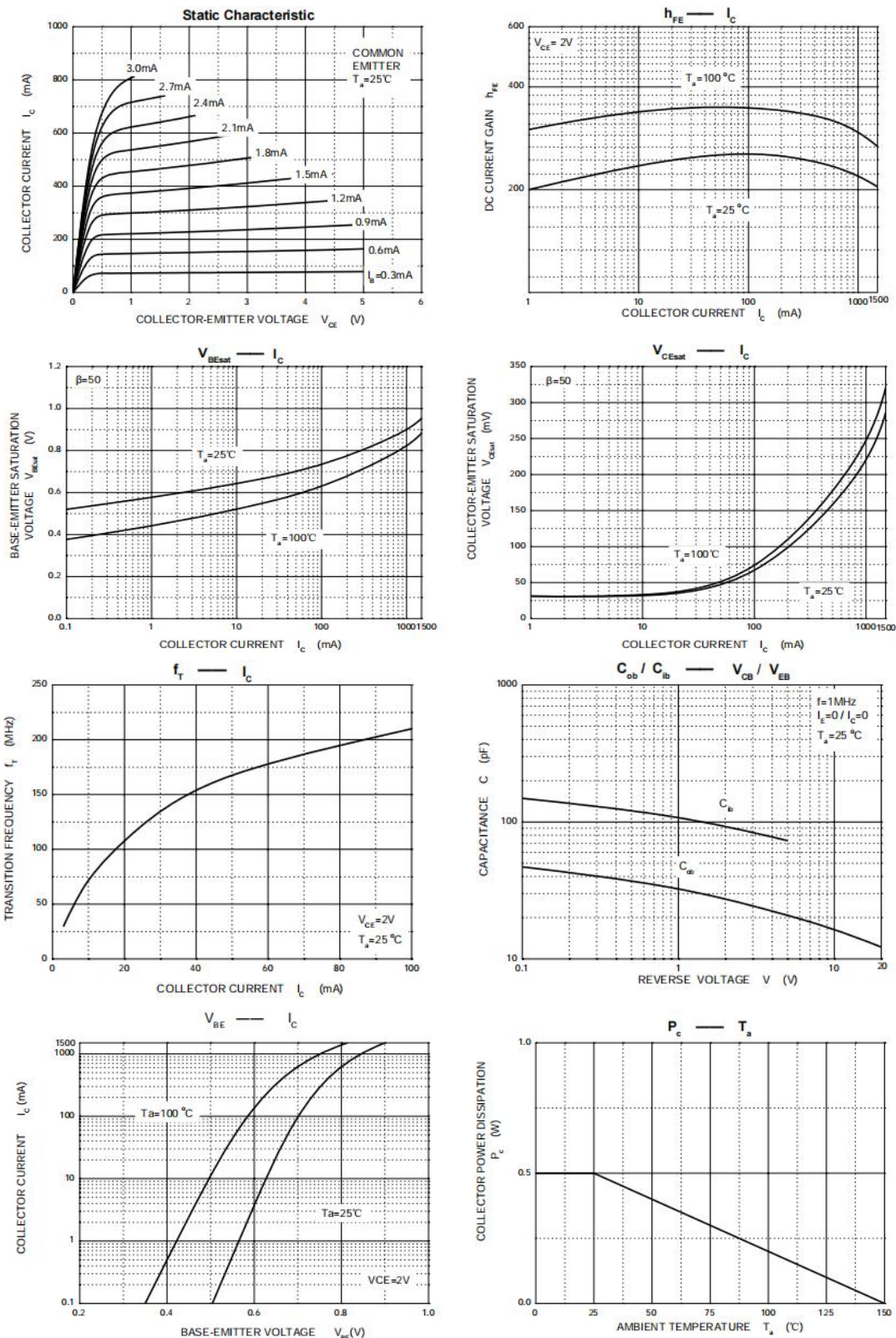


■Electrical Characteristics 电特性

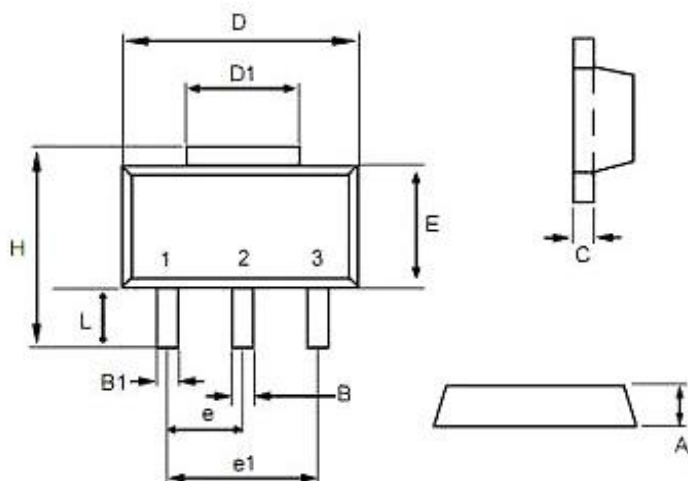
(TA=25°C unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	Min 最小值	Type 典型值	Max 最大值	Unit 单位
Collector-Base Breakdown Voltage 集电极基极击穿电压(I _C = 1mA, I _E =0)	BV _{CBO}	30	—	—	V
Collector-Emitter Breakdown Voltage 集电极发射极击穿电压(I _C = 10mA, I _B =0)	BV _{CEO}	30	—	—	V
Emitter-Base Breakdown Voltage 发射极基极击穿电压(I _E = 1mA, I _C =0)	BV _{EBO}	5	—	—	V
Collector-Base Leakage Current 集电极基极漏电流(V _{CB} = 30V, I _E =0)	I _{CBO}	—	—	0.1	μA
Emitter-Base Leakage Current 发射极基极漏电流(V _{EB} = 5V, I _C =0)	I _{EBO}	—	—	0.1	μA
DC Current Gain 直流电流增益(V _{CE} = 2V, I _C = 500mA)	H _{FE}	100	—	320	
Collector-Emitter Saturation Voltage 集电极发射极饱和压降(I _C = 1.5A, I _B = 30mA)	V _{CE(sat)}	—	—	2	V
Base-Emitter Saturation Voltage 基极发射极饱和压降(I _C = 1.5A, I _B = 30mA)	V _{BE(sat)}	—	—	2	V
Base-Emitter On Voltage 基极发射极导通电压(V _{CE} = 2V, I _C = 500mA)	V _{BE(on)}	—	—	2	V
Transition Frequency 特征频率(V _{CE} = 2V, I _C = 500mA)	f _T	—	120	—	MHz
Output Capacitance 输出电容(V _{CB} = 10V, I _E =0, f=1MHz)	C _{ob}	—	40	—	pF

■ Typical Characteristic Curve 典型特性曲线



■Dimension 外形封装尺寸



Dim	min	max
A	1.40	1.60
B	0.40	0.56
B1	0.35	0.48
C	0.35	0.44
D	4.40	4.60
D1	1.35	1.83
e	1.50 BSC	
e1	3.00 BSC	
E	2.29	2.60
H	3.75	4.25
L	0.80	1.20